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APPLICATION N	Ю.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
09/903,339	03,339 07/10/2001		Naoto Kusumoto	07977-010004	8970		
26171	7590	02/12/2004		EXAM	EXAMINER		
		DSON P.C.	DOAN, THERESA T				
1425 K S 11TH FL	TREET, N OOR	ı.w.	ART UNIT	PAPER NUMBER			
WASHIN	IGTON, I	OC 20005-3500	2814				
			DATE MAILED: 02/12/2004				

Please find below and/or attached an Office communication concerning this application or proceeding.

					Ar.
		Application No.		Applicant(s)	
		09/903,339		KUSUMOTO ET A	L.
Office Action	Summary	Examiner		Art Unit	
		Theresa T Doan		2814	
The MAILING DATE Period for Reply	of this communication app	ears on the cover	sheet with the c	orrespondenc ad	dress
A SHORTENED STATUTO THE MAILING DATE OF T - Extensions of time may be available after SIX (6) MONTHS from the may - If the period for reply specified about If NO period for reply is specified a - Failure to reply within the set or ext - Any reply received by the Office late	HIS COMMUNICATION. e under the provisions of 37 CFR 1.13 iling date of this communication. we is less than thirty (30) days, a reply oove, the maximum statutory period w ended period for reply will, by statute, er than three months after the mailing	36(a). In no event, howe y within the statutory mir vill apply and will expire , cause the application to	iver, may a reply be tim imum of thirty (30) days SIX (6) MONTHS from to become ABANDONED	ely filed will be considered timely the mailing date of this co (35 U.S.C. § 133).	
earned patent term adjustment. Se Status	e 3/ CFR 1./04(b).				
1) Responsive to com	munication(s) filed on 15 J	lanuary 2004 .			
2a) This action is FINA	L. 2b)⊠ Th	is action is non-fi	nal.		
	on is in condition for allowa ce with the practice under				e merits is
4)⊠ Claim(s) <u>1-30</u> is/are	pending in the application	1.			
. , ,	m(s) <u>1-24</u> is/are withdrawr		ion.		
5) Claim(s) is/ar					
6)⊠ Claim(s) <u>25-30</u> is/are					
7) Claim(s) is/ar					
•	subject to restriction and/o	r election require	ment.		
Application Papers	•	·	٠	·	
9) The specification is o	bjected to by the Examine	r.			
10)☐ The drawing(s) filed o	on is/are: a)□ accep	oted or b) object	ed to by the Exar	miner.	
	quest that any objection to the				
11) The proposed drawin	g correction filed on	_ is: a)□ approv	ed b)□ disappro	ved by the Examin	er.
	d drawings are required in rep	•	tion.		
12)☐ The oath or declaration	on is objected to by the Ex	aminer.			
Priority under 35 U.S.C. §§ 1					
13) Acknowledgment is	made of a claim for foreigr	n priority under 3	5 U.S.C. § 119(a)-(d) or (f).	
a)⊠ All b)□ Some *	c) None of:				
•	es of the priority document				
	es of the priority document				
application	certified copies of the prior of from the International Bu or is a list	reau (PCT Rule	17.2(a)).		Stage
14) ☐ Acknowledgment is m	ade of a claim for domesti	ic priority under 3	5 U.S.C. § 119(e	e) (to a provisional	application).
a) ☐ The translation of 15)☐ Acknowledgment is m	of the foreign language pro nade of a claim for domest				
Attachment(s)					
Notice of References Cited (PT 2) Notice of Draftsperson's Patent 3) Information Disclosure Statement	Drawing Review (PTO-948)	4) 5) 2/16/03 . 6)	•	(PTO-413) Paper Not Patent Application (PT	

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DETAILED ACTION

Request for Continued Examination

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 02/15/04 has been entered. An action on the RCE follows.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) do not apply to the examination of this application as the application being examined was not (1) filed on or after November 29, 2000, or (2) voluntarily published under 35 U.S.C. 122(b). Therefore, this application is examined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

3. Claims 25-27 are rejected under 35 U.S.C. 102(e) as being anticipated by Zhang et al. (5,508,209) as previous cited.

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Zhang et al. teach in figures 5A-5F a method of manufacturing a semiconductor device comprising the steps of:

forming an amorphous silicon semiconductor film 203 over a substrate 201;

irradiating the amorphous silicon semiconductor film with a second harmonic of a continuous wave laser comprising Nd which is an Nd:YAG laser to crystallize the amorphous semiconductor film (column 9, lines 3-10); and

patterning the crystallized semiconductor film 203 to form an active layer including at least a channel formation region (see figure 5C).

Double Patenting

4. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970);and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

5. Claims 25-30 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 17-21, 22-27, 34-43, 48-56 and 61-80 of U. S. Patent No. 6,204,099. Although the conflicting claims are not identical, they are not patentably distinct from each other because as follows: both U.S.

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Patent and instant application claimed a method of manufacturing a semiconductor layer comprises amorphous silicon. Moreover, the claims 61-80 in the U.S. No. 6,204,099 are either narrower version of the claims of the instant application or obvious variations thereof. For example, claims 63 and 68 in U.S. No. 6,204,099 "... said semiconductor film comprises amorphous silicon (claim 63)" and whereas claim 26 in the instant application claims "... wherein said amorphous semiconductor film comprises amorphous silicon", that shows no different meaning between these two elements. The facts are that the claims of the U. S. Patent No. 6,204,099 and instant application have claimed the same goal and are not distinguished from each other.

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Response to Arguments

- 6. Applicant argues that "Zhang summarily dismisses a continuous oscillated laser as a non-preferred embodiment and then provides examples of only the preferred embodiment; namely the pulse laser". This argument is not persuasive because Zhang (column 9, lines 1-7) clearly discloses that "The laser does not need to be limited to an excimer laser, and other lasers are also usable", including "a continuous oscillated laser", but "a pulsed laser" is preferred. Therefore, Zhang does not dismiss the use of "a continuous oscillated laser" as asserted by Applicant, but rather, Zhang suggest the use of both "a continuous oscillated laser" and "a pulsed laser", but "a pulsed laser" is preferred.
- 7. Regarding the rejection under obviousness-type double patenting, Applicant's argument that Kusumoto does not recite the step of "patterning the crystallized

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semiconductor film to form an active layer including at least a channnel formation region". This argument is not persuasive because the above limitations are disclosed in claim 78 of Kusumoto. Therefore, the double patenting as it applies to U.S. Patent No. 6,204,099 is still proper.

The rest of applicant's arguments, addressed to the amended claims are considered in the rejections shown above.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Theresa T Doan whose telephone number is (571) 272-1704. The examiner can normally be reached on Monday to Thursday from 8:00AM - 6:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, WAEL FAHMY can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (571) 272-1562.

TD February 3, 2004.

PHAT X. CAO Primary Examiner.